CLARATION FOR PATENT APPL TION

As a below named inventor(s),	I (we) hereby declare that:			
My (our) residence(s), post off name(s).	ice address(es) and citizenship(s) is (are) the same as stated b	pelow next to my (our)	
and joint inventor (if plural nar	n original, first and sole inventor nes are listed below) of the subj d: SILICON WAFER, AND MA	ect matter which is claimed and	d for which a patent is	
the specification of which is at	tached hereto unless the followi	ng box is checked:	•	
[] was filed on	as United Stat	es Application Number	or	
PCT International App	lication Number	·		
and was amended on	(if ap	oplicable).		
I (we) hereby state that I (we) including the claims, as amend	have reviewed and understand ded by any amendment referred	the contents of the above ident I to above	ified specification,	
I (we) acknowledge the duty to Federal Regulations, §1.56.	disclose information which is n	naterial to patentability as defin	ed in Title 37, Code of	
application(s) for patent or inv	ority benefits under Title 35, Un entor's certificate listed below a having a filing date before that	nd have also identified below a	ny foreign application for	
	Prior Foreign Application(s):			
(Number)	(Country)	(Day/Month/Year)	Priority Claimed: YES NO	
				
		·		
I (we) hereby claim the benefit application(s) listed below:	t under Title 35, United States C	Code, §119(e) of any United Sta	ates provisional	
	(Application Number)	(Filin	g Date)	
below and, insofar as the subjectates application in the mannacknowledge the duty to disclo	t under Title 35, United States Cect matter of each of the claims er provided by the first paragrapse information which is materiane available between the filing application.	of this application is not disclo ph of Title 35, United States Co Il to patentability as defined in	sed in the prior United ode, § 112, I (we) Title 37, Code of Federal	
(Application Serial No.)	(Filing date)	(STATUS-patented	(STATUS-patented, pending, abandoned)	

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I (we) hereby appoint the following attorney(s) and/or agent(s) to prosecute this application and to transact all business in the Patent and Trademark Office connected therewith and to act in accordance with the instructions from Suda Patent Office:

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I (we) hereby declare that all statements made herein of my (our) own knowledge are true, and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

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Inventor's signature:

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g:	Da Da	te:		
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Post Office Address:				
Inventor's signature: Date:				
Full name of 8th inventor (given name, family name):				
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Post Office Address:				
Inventore signatur	a.	Da	ta	